

FLL400IK-2C

High Voltage - High Power GaAs FET

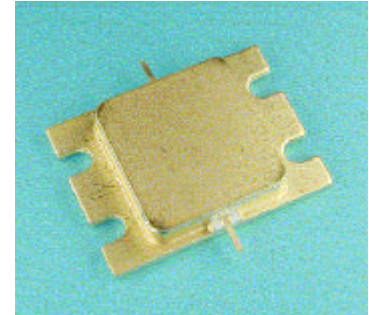
FEATURES

- High Output Power: P1dB=46.0dBm(Typ.)
- High Gain: G1dB=13.0dB(Typ.)
- High PAE: η_{add} =45%(Typ.)
- Broad Band: 2.11~2.17GHz
- Hermetically Sealed Package

DESCRIPTION

The FLL400IK-2C is a 40 Watt GaAs FET that is specially suited for use in W-CDMA base station amplifier as long term reliability.

Fujitsu's stringent Quality Assurance Program assures the highest reliability and consistent performance.



ABSOLUTE MAXIMUM RATING (Case Temperature Tc=25°C)

Item	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	15	V
Gate-Source Voltage	V _{GS}	-5	V
Total Power Dissipation	P _{Tot}	100	W
Storage Temperature	T _{stg}	-65 to +175	°C
Channel Temperature	T _{ch}	175	°C

RECOMMENDED OPERATING CONDITION (Case Temperature Tc=25°C)

Item	Symbol	Condition	Limit	Unit
DC Input Voltage	V _{DS}		12	V
Forward Gate Current	I _{GF}	R _G =5W	<85	mA
Reverse Gate Current	I _{GR}	R _G =5W	>-25	mA
Operating channel temperature	T _{ch}		145	°C

ELECTRICAL CHARACTERISTICS (Case Temperature Tc=25°C)

Item	Symbol	Condition	Limit			Unit
			Min.	Typ.	Max.	
Pinch-off Voltage	V _p	V _{DS} =5V, I _{DS} =110mA	-0.1	-0.3	-0.5	V
Gate-Source Breakdown Voltage	V _{GSO}	I _{GS} =-1.1mA	-5.0	-	-	V
Output Power at 1dB G.C.P.	P1dB	V _{DD} =12V f=2.17GHz I _{DS} (DC)=1.5A Pin=35dBm	45.0	46.0	-	dBm
Power Gain at 1dB G.C.P.	G1dB		12.0	13.0	-	dB
Drain Current	I _{dsr}		-	6.7	8.7	A
Power-added Efficiency	η_{add}		-	45.0	-	%
Thermal Resistance	R _{th}		-	1.3	1.5	°C/W

CASE STYLE: IK

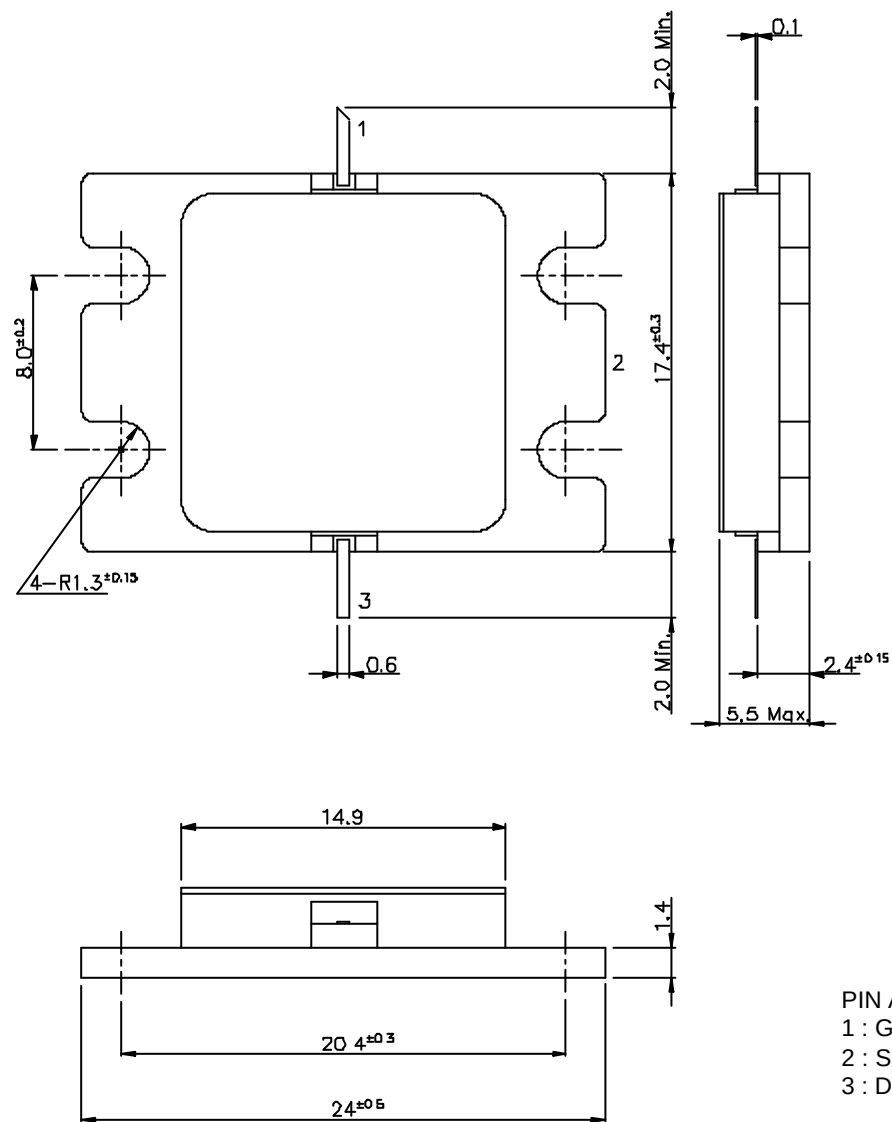
ESD	Class III	2000 V~
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Note : Based on EIAJ ED-4701 C-111A(C=100pF, R=1.5kΩ)

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■ Package Out Line



PIN ASSIGNMENT
1 : GATE
2 : SOURCE(Flange)
3 : DRAIN

Unit:mm

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For further information please contact :

Eudyna Devices USA Inc.
2355 Zanker Rd.
San Jose, CA 95131-1138, U.S.A.
Phone: (408) 232-9500
FAX: (408) 428-9111
www.fcsi.fujitsu.com

Eudyna Devices Europe Ltd.
Network House
Norreys Drive
Maidenhead, Berkshire SL6 4FJ
Phone: +44 (0) 1628 504800
FAX: +44 (0) 1628 504888

Eudyna Devices Asia Pte. Ltd. Hong Kong Branch

Rm.1101,Ocean Centre, 5 Canton Road, Tsim Sha Tsui Kowloon, Hong kong
Tel: +852-2377-0227
Fax: +852-2377-3921

Eudyna Devices Inc.

1000 Kamisukiahara, showa-cho, Nakakomagun, Yamanashi
409-3883, Japan
(Kokubo Industrial Park)
Tel +81-55-275-4411
Fax +81-55-275-9461

Sales Division

1,Kanai-cho,Sakae-ku,Yokohama,244-0845,Japan
Tel +81-45-853-8156
Fax +81-45-853-8170

CAUTION

Fujitsu Compound Semiconductor Products contain **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment.

For safety, observe the following procedures:

Do not put these products into the mouth.

Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.

Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.